

NOT RECOMMENDED FOR NEW DESIGN USE DMP4011SK3Q



DMP4015SK3Q

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D T _C = +25°C	
-40V	$11m\Omega @ V_{GS} = -10V$	-35A	
-4 0V	$15m\Omega$ @ $V_{GS} = -4.5V$	-30A	

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Backlighting

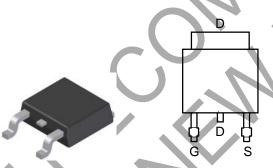
Features and Benefits

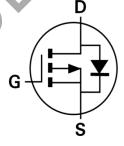
- 100% Unclamped Inductive Switch (UIS) Test In Production
- Low On-Resistance
- · Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (€3)
- Weight: 0.33 grams (Approximate)

TO252 (DPAK)





Equivalent Circuit

Ordering Information (Notes 4 & 5)

Part Number	Compliance	Case	Packaging
DMP4015SK3Q-13	Automotive	TO252 (DPAK)	2500/Tape & Reel

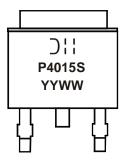
Γορ View Pin-Out

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information



O!! = Manufacturer's Marking
P4015S = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 18 = 2018)
WW = Week (01 - 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage			V_{DSS}	-40	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	lo.	-35 -27	А
Continuous Drain Current (Note C) V 40V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	ID	-14 -11	А
Continuous Drain Current (Note 6) V _{GS} = -10V	t<10s	$T_A = +25$ °C $T_A = +70$ °C	lo	-22 -18	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-100	Α
Maximum Body Diode Forward Current (Note 6)			ls	-5.5	Α
Avalanche Current (Note 7)			l _{AS}	-22	Α
Avalanche Energy (Note 7)			E _{AS}	242	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	$T_A = +25$ °C	D-	3.5	W
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	P _D	2.2	VV
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	36	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	R _{OJA}	15	°C/W
Thermal Resistance, Junction to Case (Note 6)	Steady State	R _{OJC}	4.5	
Operating and Storage Temperature Range	•	T _{J,} T _{STG}	-55 to +150	°C

Notes:

- 6. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 7. UIS in production with L = 0.1mH, $T_J = +25$ °C.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

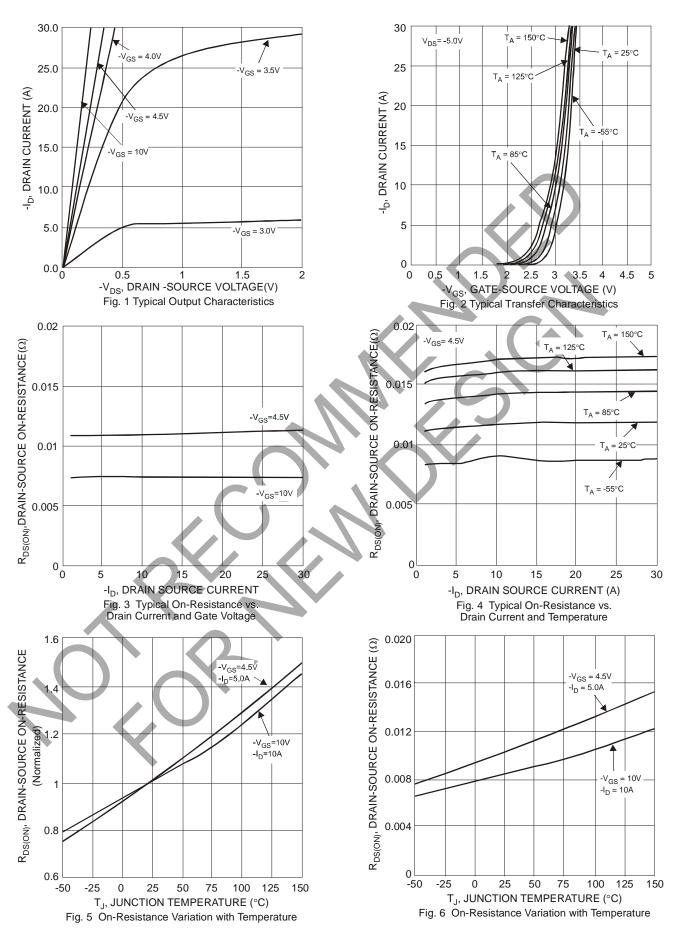
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	-40	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}		_	-1	μΑ	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	1	_	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(th)}	-1.5	-2	-2.5	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
Static Drain-Source On-Resistance	5	_	7	11	mΩ	$V_{GS} = -10V, I_D = -9.8A$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}	-	9	15	11122	$V_{GS} = -4.5V$, $I_D = -9.8A$	
Forward Transfer Admittance	Y _{fs}		26	_	S	$V_{DS} = -20V, I_D = -9.8A$	
Diode Forward Voltage	V_{SD}	-	-0.7	-1	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	4,234	_		201/1/	
Output Capacitance	Coss		1,036	_	pF	$V_{DS} = -20V, V_{GS} = 0V$ f = 1MHz	
Reverse Transfer Capacitance	Crss	_	526	_		1 = 11/11/12	
Gate Resistance	R_{G}	-	7.77	`	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_g	_	47.5	_		$V_{DS} = -20V, V_{GS} = -5V$ $I_{D} = -9.8A$	
Gate-Source Charge	Q_{gs}		14.2	1	nC		
Gate-Drain Charge	Q_{gd}	_	13.5				
Turn-On Delay Time	t _{D(on)}		13.2	/			
Turn-On Rise Time	t _r	_	10		~~	$V_{GS} = -10V, V_{DD} = -20V,$	
Turn-Off Delay Time	t _{D(off)}	_	302.7		nS	$R_G = 6\Omega$, $I_D = -1A$	
Turn-Off Fall Time	t _f		137.9	V -			

Notes:

- 8. Short duration pulse test used to minimize self-heating effect. 9. Guaranteed by design. Not subject to production testing.









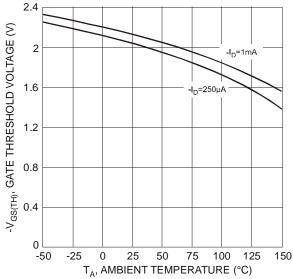
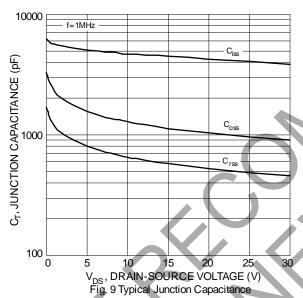
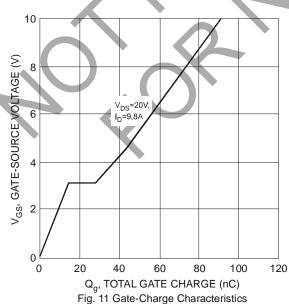
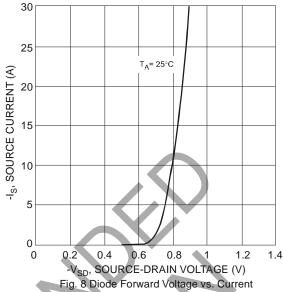


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







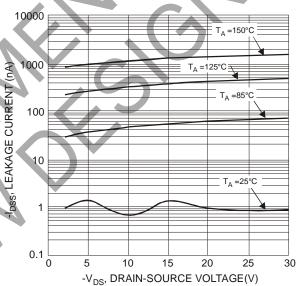


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

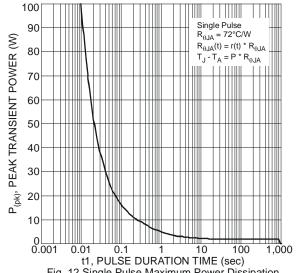
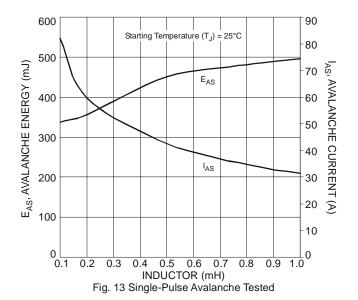
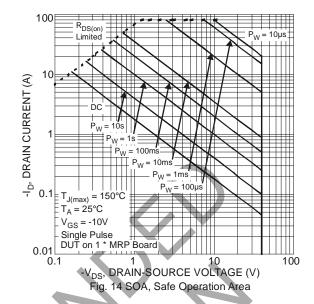
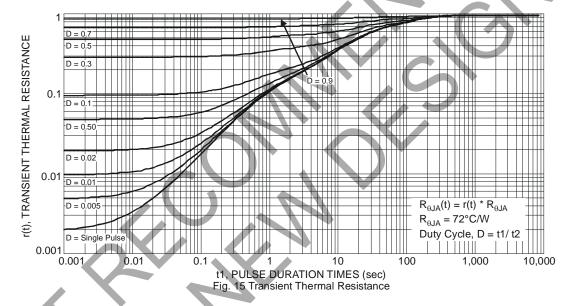


Fig. 12 Single Pulse Maximum Power Dissipation











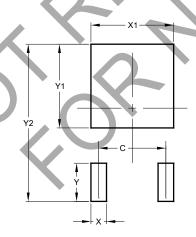
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)						
Dim	Min	Max	Тур			
Α	2.19	2.39	2.29			
A1	0.00	0.13	0.08			
A2	0.97	1.17	1.07			
q	0.64	0.88	0.783			
b2	0.76	1.14	0.95			
b3	5.21	5.46	5.33			
o	0.45	0.58	0.531			
D	6.00	6.20	6.10			
D1	5.21	_				
е	_	1	2.286			
П	6.45	6.70	6.58			
E1	4.32					
I	9.40	10.41	9.91			
Γ	1.40	1.78	1.59			
L3	0.88	1.27	1.08			
L4	0.64	1.02	0.83			
a	0°	▶ 10°				
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
	` ,
С	4.572
Х	1.060
X1	5.632
Υ	2.600
Y1	5.700
V2	10.700

TO252 (DPAK)



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